

# **RJK1021DPN**

# N-Channel Power MOSFET High-Speed Switching Use

REJ03G1628-0100 Rev.1.00 Apr 02, 2008

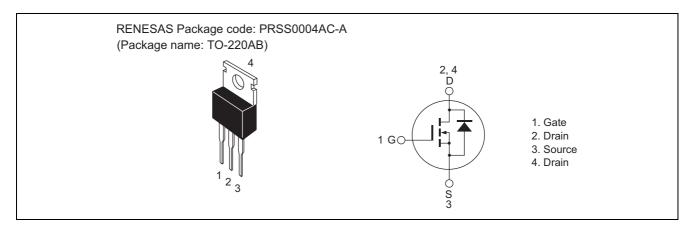
### **Features**

• V<sub>DSS</sub>: 100 V

•  $R_{DS(on)}$ : 20 m $\Omega$  (Max)

• I<sub>D</sub>: 70 A

### **Outline**



# **Application**

• Motor control, Solenoid control, DC-DC converter, etc.

### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	100	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	I <sub>D</sub>	70	А
Drain peak current	I <sub>D (pulse)</sub>	140	А
Body-drain diode reverse drain current	I <sub>DR</sub>	70	А
Body-drain diode reverse drain peak current	I <sub>DR (pulse)</sub>	140	А
Avalanche current	I <sub>AP</sub> Note2	35	А
Channel dissipation	Pch Note1	100	W
Channel to case thermal impedance	θch-c	1.25	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. Value at Tc = 25°C

2. STch = 25°C, Tch  $\leq$  150°C, L = 100  $\mu H$ 

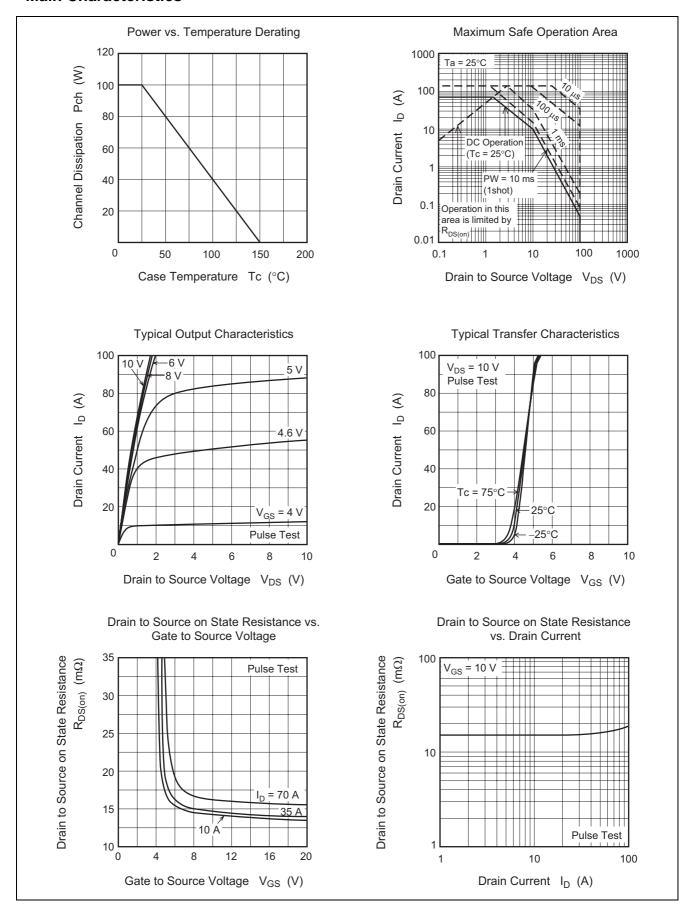
# **Electrical Characteristics**

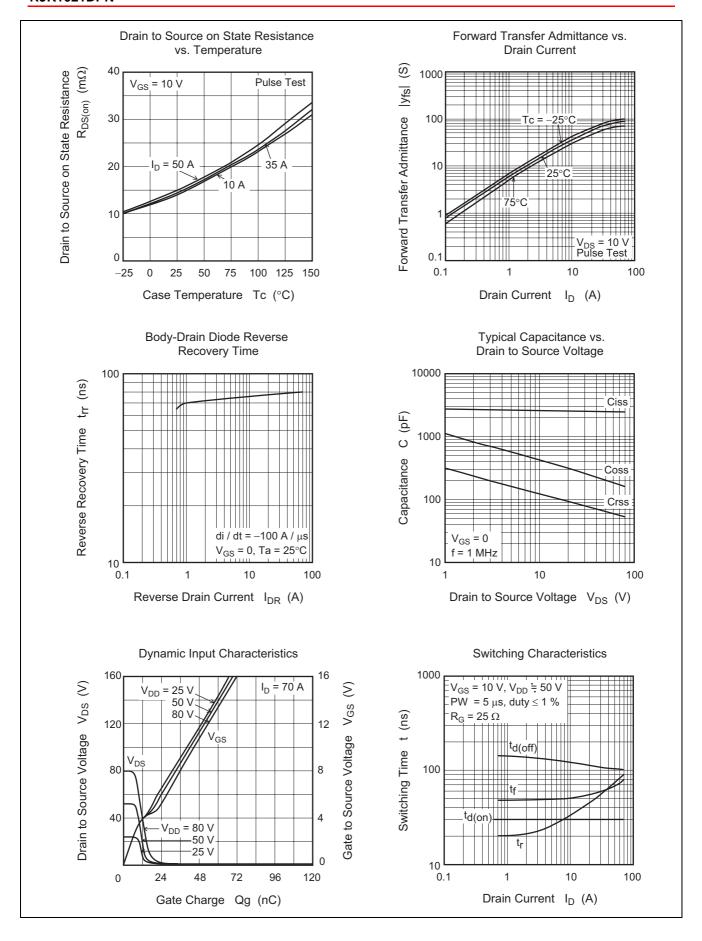
 $(Ta = 25^{\circ}C)$ 

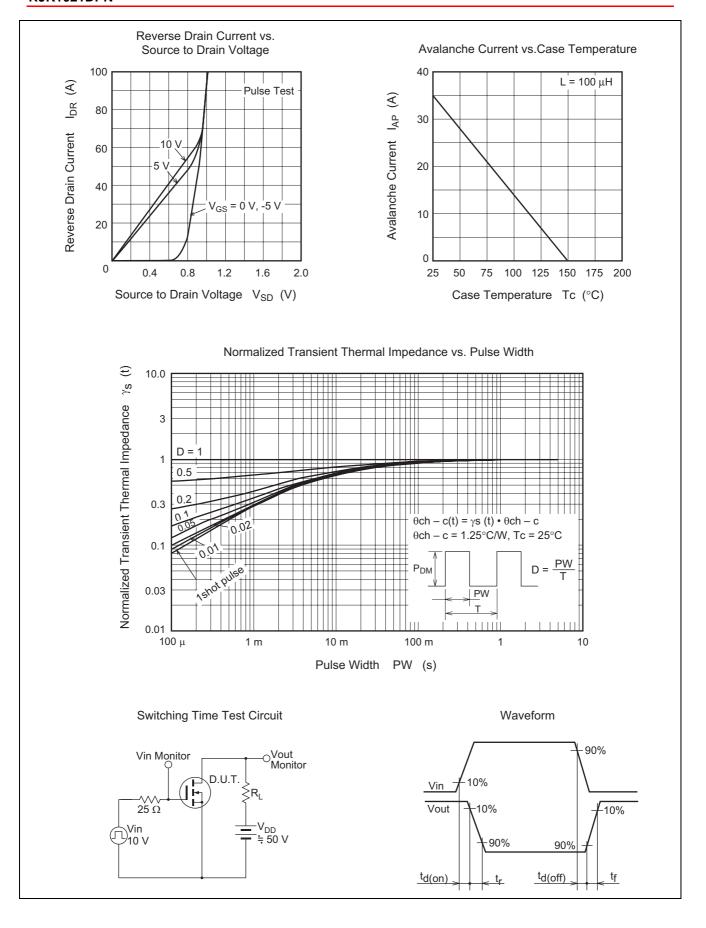
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	_	_	V	$I_D = 1 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	100	μΑ	$V_{DS} = 100 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	3.0	4.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}^{\text{Note3}}$
Static drain to source on state voltage	$V_{DS(on)}$	_	0.56	0.70	V	$I_D = 35 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$
Static drain to source on state	R <sub>DS(on)</sub>	_	16	20	mΩ	$I_D = 35 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$
resistance						
Input capacitance	Ciss	_	2600	_	pF	V <sub>DS</sub> = 10 V
Output capacitance	Coss	_	430	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	160	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d(on)</sub>	_	30	_	ns	V <sub>DD</sub> = 50 V
Rise time	t <sub>r</sub>	_	70	_	ns	I <sub>D</sub> = 35 A
Turn-off delay time	t <sub>d(off)</sub>	_	110	_	ns	$V_{GS} = 10 \text{ V}$
Fall time	t <sub>f</sub>	_	65	_	ns	$R_G = 25 \Omega$
Body-drain diode forward voltage	$V_{DF}$	_	0.9	1.5	V	$I_F = 35 \text{ A}, V_{GS} = 0$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	80	_	ns	$I_F = 70 \text{ A}, V_{GS} = 0$
						$di_F/dt = 100 A/\mu s$

Notes: 3. Pulse test

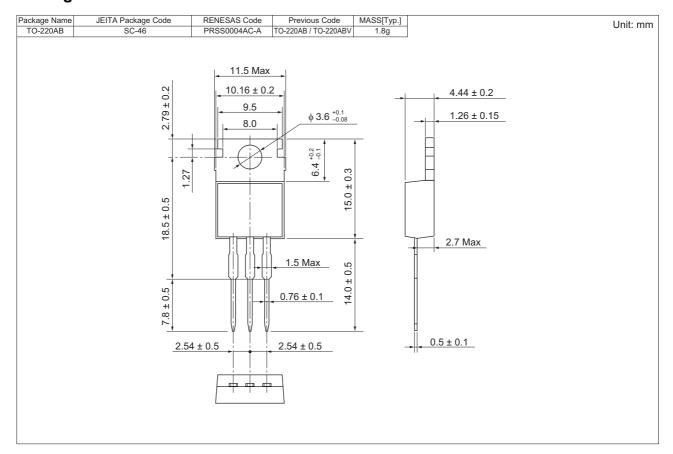
### **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK1021DPN-00-00	500 pcs	Box (Sack)

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